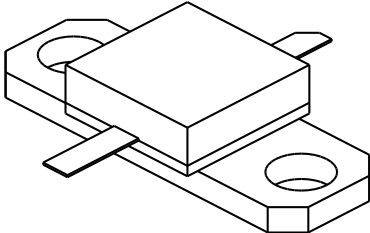


<p><b>GENERAL DESCRIPTION</b> The 1014-12 is a COMMON BASE transistor capable of providing 12 Watts of Class C, RF output power over the band 1000-1400 MHz. This transistor is designed for Microwave Broadband Class C amplifier applications. It includes input prematching and utilizes gold metalization and diffused ballasting to provide high reliability and supreme ruggedness.</p>	<p><b>CASE OUTLINE</b> <b>55LT, STYLE 1</b></p> 
<p><b>ABSOLUTE MAXIMUM RATINGS</b></p> <p>Maximum Power Dissipation @ 25°C <span style="float: right;">39 Watts</span></p> <p><b>Maximum Voltage and Current</b></p> <p>BVces Collector to Emitter Voltage <span style="float: right;">50 Volts</span>          BVebo Emitter to Base Voltage <span style="float: right;">3.5 Volts</span>          Ic Collector Current <span style="float: right;">5.0 A</span></p> <p><b>Maximum Temperatures</b></p> <p>Storage Temperature <span style="float: right;">- 65 to +150°C</span>          Operating Junction Temperature <span style="float: right;">+200°C</span></p>	

**ELECTRICAL CHARACTERISTICS @ 25 °C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>Pout</b>	Power Out	F = 1000-1400 MHz	12			Watt
<b>Pin</b>	Power Input	Vcc = 28 Volts			2.5	Watt
<b>Pg</b>	Power Gain	Pin = 2.5 Watts	6.8			dB
$\eta_c$	Collector Efficiency	As Above		40		%
<b>VSWR<sub>1</sub></b>	Load Mismatch Tolerance	F = 1.4 GHz, Pin = 2.5 W			30:1	

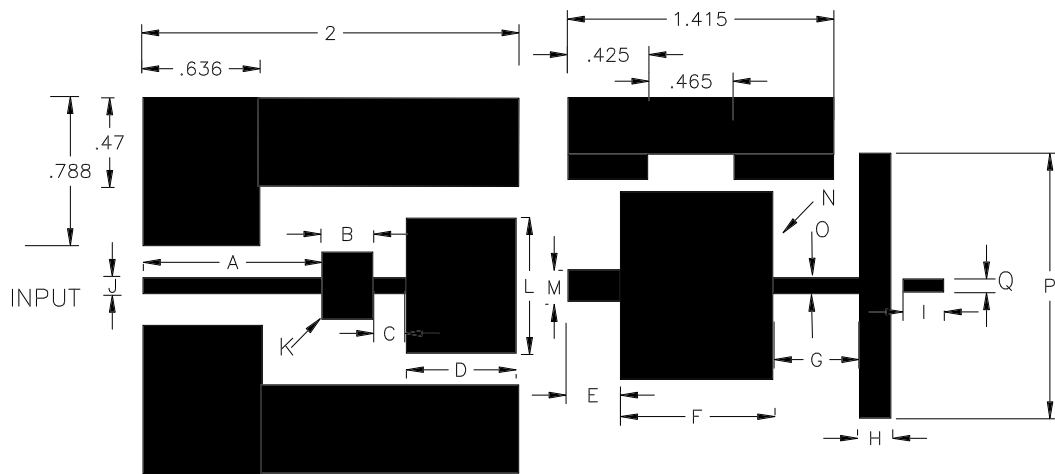
<b>BVces</b>	Collector to Emitter Breakdown	Ic = 5 mA	50			Volts
<b>BVebo</b>	Emitter to Base Breakdown	Ie = 5 mA	3.5			Volts
<b>Icbo</b>	Collector to Base Current	Vcb = 28 Volts			3.0	mA
<b>h<sub>FE</sub></b>	Current Gain	Vce = 5 V, Ic = 200mA	10			
<b>Cob</b>	Output Capacitance	F = 1 MHz, Vcb = 28 V		12.0		pF
$\theta_{jc}$	Thermal Resistance				4.5	°C/W

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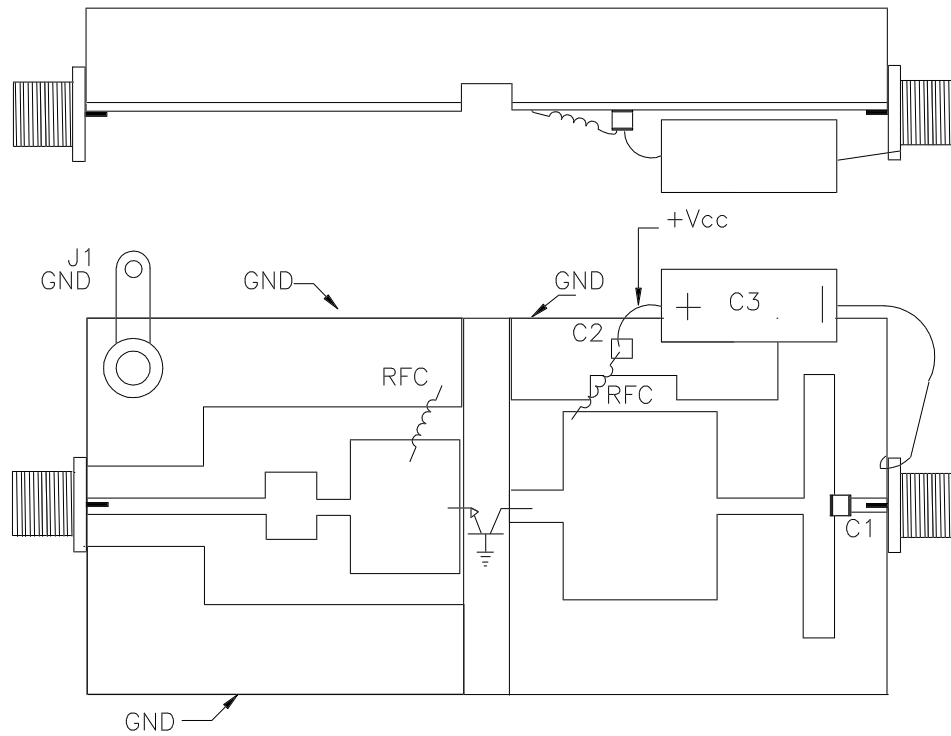
REVISIONS

ZONE	REV	DESCRIPTION	DATE	APPROVED
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DIM	INCHES
A	.960
B	.270
C	.180
D	.590
E	.280
F	.810
G	.460
H	.168
I	.217
J	.085
K	.360
L	.720
M	.170
N	1.00
O	.085
P	1.41
Q	.063

1014-12 TEST CIRCUIT



DIELECTRIC = 20 MIL THICK DUROID (Hardback) Er = 2.33

C1=150 pF chip

C2=18 pF chip

C3= 50uF, 50v dc, electrolytic

RFC= 6 turns, .1 in dia., #24 ga. enamel wire



CAGE  
0PJR2

DWG NO.

1014-12

REV

2

SCALE

1/1

SHEET